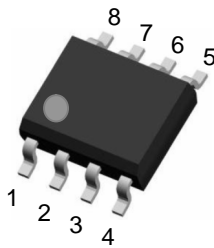


Dual P-Channel Enhancement-Mode MOSFET (-30V, -5.3A)

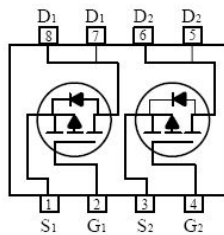
PRODUCT SUMMARY		
V_{DS}	I_D	$R_{DS(on)}$ (m-ohm) Max
-30V	-5.3A	60 @ $V_{GS} = -10V, I_D = -5.3A$
		85 @ $V_{GS} = -4.5V, I_D = -3.9A$

Features

- Advanced Trench Process Technology
- High Density Cell Design for Ultra Low On-Resistance
- Surface mount Package
- Ordering information : KF4953 (Lead (Pb) -free)
KF4953-G (Lead (Pb) -free and halogen-free)



SOP-8



Pin 1: Source 2
Pin 2: Gate 2
Pin 3: Source 1
Pin 4: Gate 1
Pin 5 / 6: Drain 1
Pin 7 / 8: Drain 2

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current (Continuous)	-5.3	A
I_{DM}	Drain Current (Pulsed) ^a	-20	A
P_D	Total Power Dissipation @ $T_A = 25^\circ\text{C}$	2.0	W
I_S	Maximum Diode Forward Current	-2	A
T_j, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (PCB mounted) ^b	50	$^\circ\text{C/W}$

a: Repetitive Rating: Pulse width limited by the maximum junction temperature.
 b: 1-in² 2oz Cu PCB board